

NTBG022N120M3S

SiC MOSFET 1200 V 22 mohm M3S Series in D2PAK-7L package

Product Overview

For complete documentation, see the data sheet.

The new family of 1200V M3S planar SiC MOSFETs is optimized for fast switching applications. Planar technology works reliably with negative gate voltage drive and turn off spikes on the gate. This family has optimum performance when driven with 18V gate drive but also works well with 15V gate drive.

Features

- D2PAK-7L package for low common source inductance
- 15V to 18V Gate Drive
- New M3S technology: 22mohm RDS(ON) with low EON and EOFF losses
- 100% Avalanche Tested

Benefits

- Reduced EON losses
- 18V for best performance; 15V for compatibility with IGBT driver circuits
- Improved power density
- Improved robustness to unexpected incoming voltage spikes or ringing

Applications

- AC-DC Conversion
- DC-AC Conversion
- DC-DC Conversion

End Products

- UPS
- Electric Vehicle Chargers
- Solar Inverters
- Energy Storage Systems

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Family	Blocking Voltage BV _{DSS} (V)	I _{D(max)} (A)	R _{D(on)} Typ @ 25°C (mΩ)	Q _{g Total} (nC)	Output Capacitance (pF)	T _{j Max} (°C)	Package Type
NTBG022N120M3S	23.5594	 	NEW	M3S	1200	58	22	148	148	175	D2PAK7 (TO-263-7L HV)